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Kind regards,

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BUK7640-100A

N-channel TrenchMOS standard level FET

Rev. 2 — 20 April 2011 Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

1.3 Applications

- Automotive and general purpose power switching

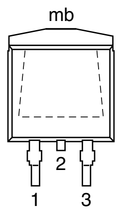
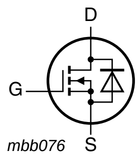
1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	-	100	V
I_D	drain current	$T_{mb} = 25$ °C	-	-	37	A
P_{tot}	total power dissipation		-	-	138	W
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 25$ °C	-	30	40	mΩ
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 26$ A; $V_{sup} \leq 25$ V; $R_{GS} = 50$ Ω; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; unclamped	-	-	31	mJ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 SOT404 (D2PAK)	
2	D	drain[1]		
3	S	source		
mb	D	mounting base; connected to drain		

[1] drain (D)

3. Ordering information

Table 3. Ordering information

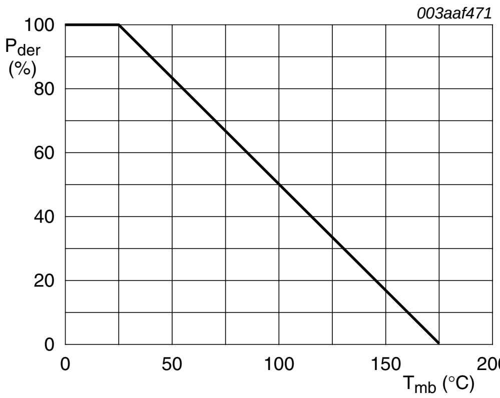
Type number	Package		
	Name	Description	Version
BUK7640-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

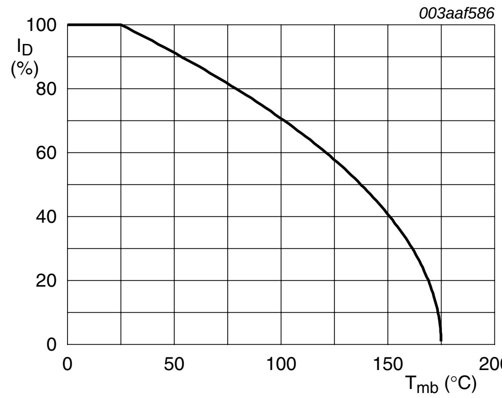
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20$ kΩ	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$T_{mb} = 25$ °C	-	37	A
		$T_{mb} = 100$ °C	-	26	A
I_{DM}	peak drain current	$T_{mb} = 25$ °C; pulsed	-	149	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C	-	138	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25$ °C	-	37	A
I_{SM}	peak source current	pulsed; $T_{mb} = 25$ °C	-	149	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 26$ A; $V_{sup} \leq 25$ V; $R_{GS} = 50$ Ω; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; unclamped	-	31	mJ



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\,\%$$

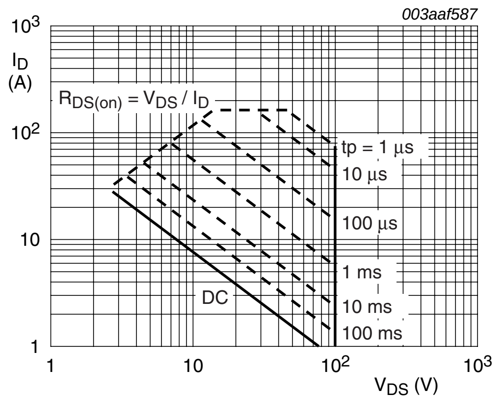
Fig 1. Normalized total power dissipation as a function of mounting base temperature



$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100\,\%$$

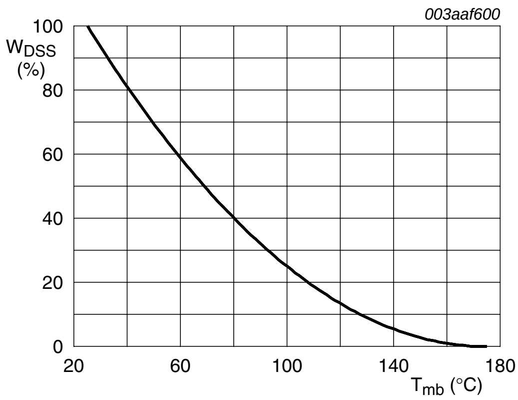
$V_{GS} \geq 10$ V

Fig 2. Normalized continuous drain current as a function of mounting base temperature



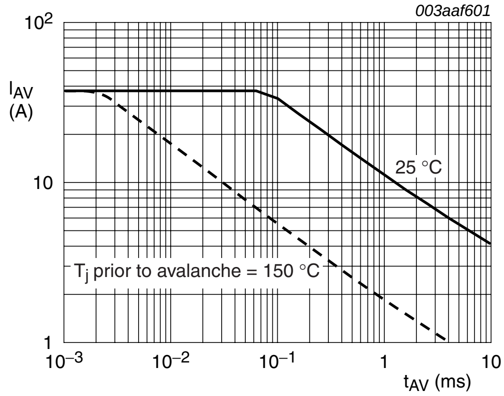
T_{mb} = 25 °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



I_D = 75 A

Fig 4. Normalised drain-source non-repetitive avalanche energy as a function of mounting-base temperature



unclamped inductive load

Fig 5. Single-shot avalanche rating; avalanche current as a function of avalanche period

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1.1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	50	-	K/W

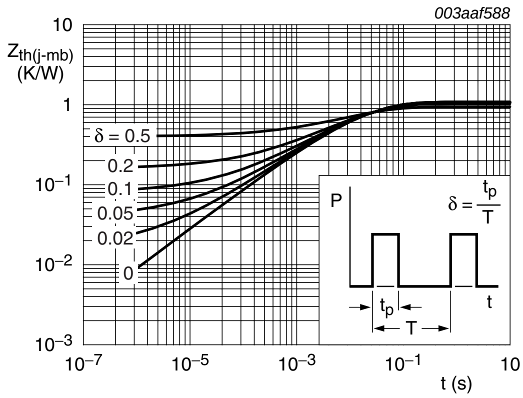
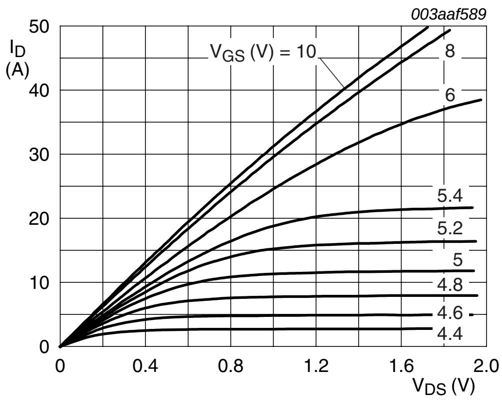


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

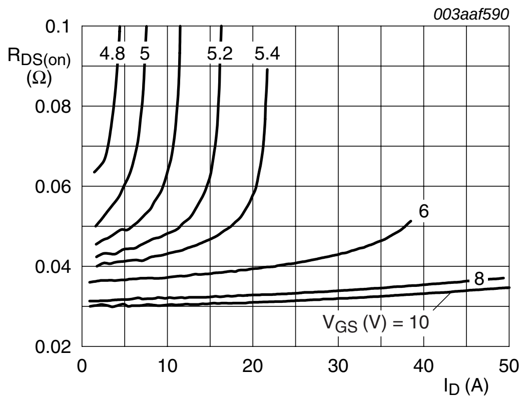
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	89	-	-	V
		I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C	2	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C	-	-	4.4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C	1	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C	-	-	108	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C	-	30	40	mΩ
Dynamic characteristics						
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C	-	1720	2293	pF
C_{oss}	output capacitance		-	216	259	pF
C_{rss}	reverse transfer capacitance		-	133	182	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω; T_j = 25 °C	-	12	18	ns
t_r	rise time		-	55	83	ns
$t_{d(off)}$	turn-off delay time		-	48	67	ns
t_f	fall time		-	30	42	ns
L_D	internal drain inductance	measured from upper edge of drain tab to centre of die; T_j = 25 °C	-	2.5	-	nH
L_S	internal source inductance	measured from source lead soldering point to source bond pad; T_j = 25 °C	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C	-	0.85	1.2	V
		I_S = 37 A; V_{GS} = 0 V; T_j = 25 °C	-	1.1	-	V
t_{rr}	reverse recovery time	I_S = 37 A; dI_S/dt = -100 A/µs; V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	70	-	ns
Q_r	recovered charge		-	0.24	-	µC



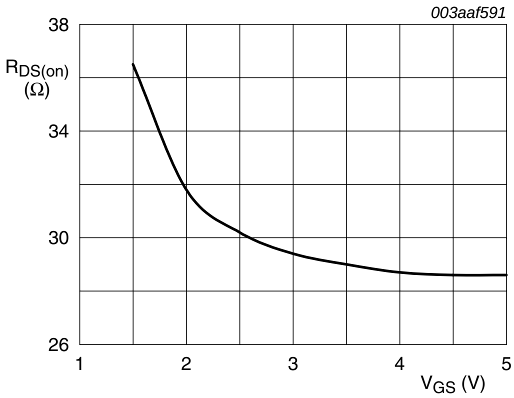
$T_j = 25$ °C

Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values



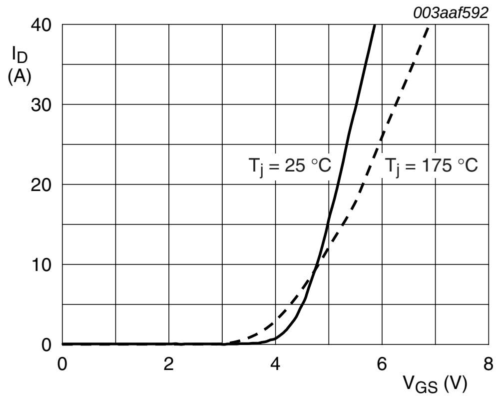
$T_j = 25$ °C

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



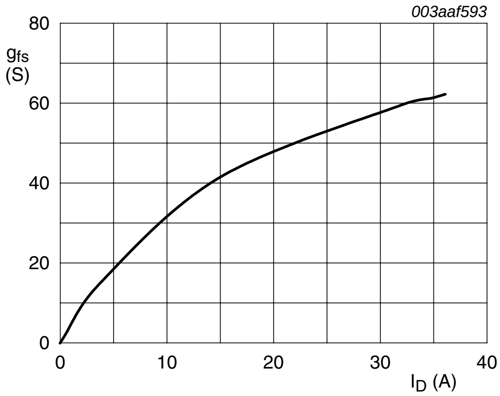
$T_j = 25$ °C; $I_D = 25$ A

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



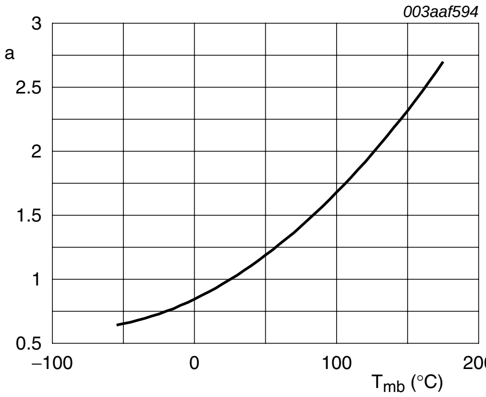
$V_{DS} > I_D \times R_{DSon}$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



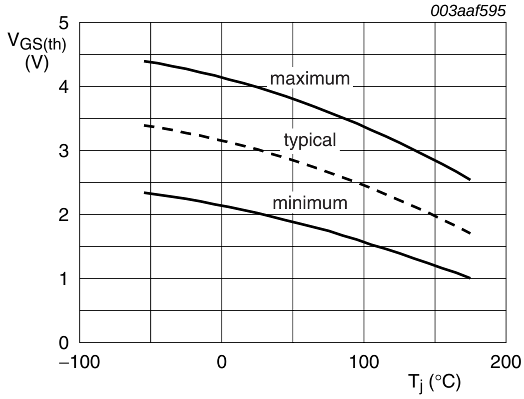
$T_j = 25$ °C; $V_{DS} > I_D \times R_{DSon}$

Fig 11. Forward transconductance as a function of drain current; typical values



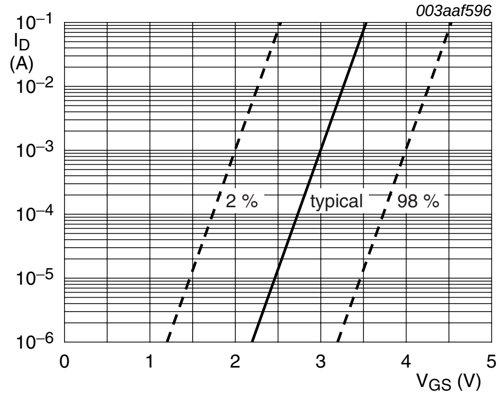
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



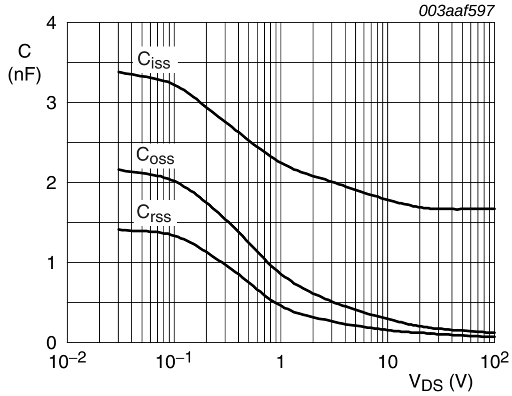
I_D = 1 mA; V_{DS} = V_{GS}

Fig 13. Gate-source threshold voltage as a function of junction temperature



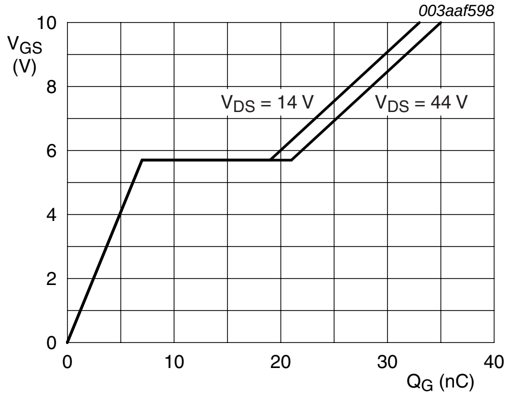
T_j = 25 °C; V_{DS} = V_{GS}

Fig 14. Sub-threshold drain current as a function of gate-source voltage



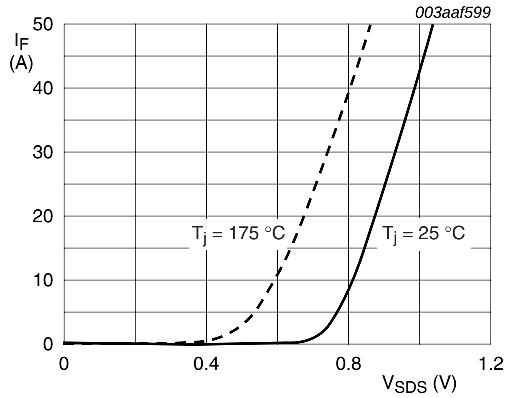
V_{GS} = 0 V; f = 1 MHz

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



T_j = 25 °C

Fig 16. Gate-source voltage as a function of gate charge; typical values

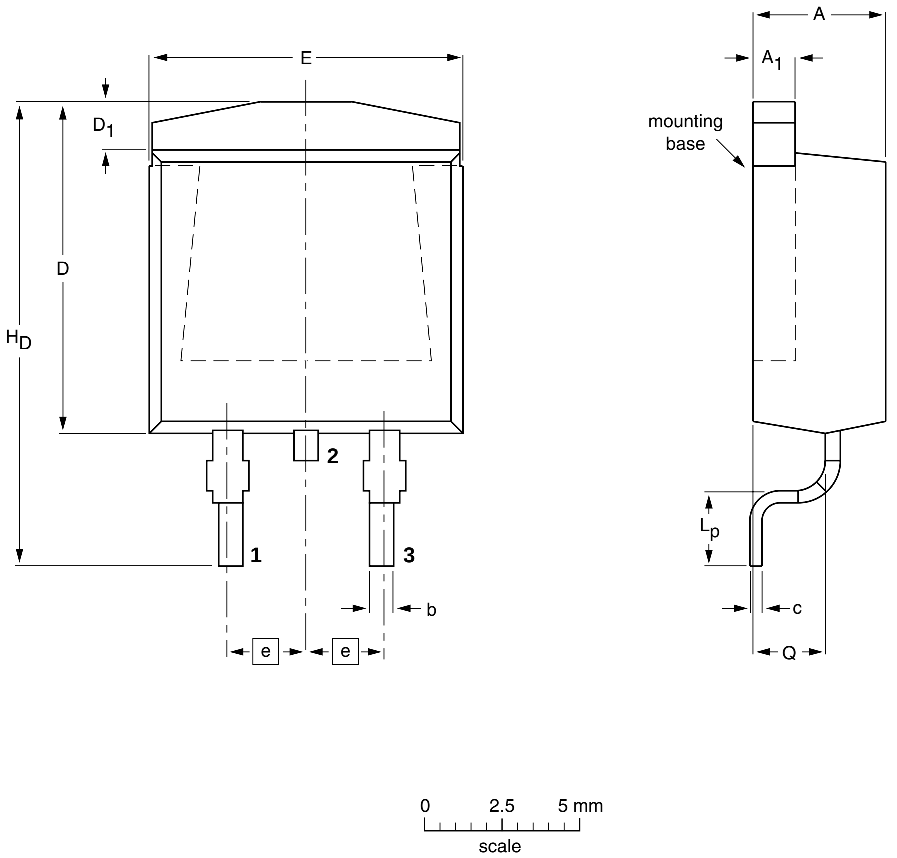


V_{GS} = 0 V

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) **SOT404**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D max.	D_1	E	e	L_p	H_D	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						~~05-02-11~~ 06-03-16

Fig 18. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7640-100A v.2	20110420	Product data sheet	-	BUK7640-100A_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate.			
BUK7640-100A_1	19991201	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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11. Contents

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